

Investigation of Dielectric Properties of $(1-x)\text{Ba}_{0.7}\text{Sr}_{0.3}\text{TiO}_3 \cdot x\text{MgZrO}_3$ Ceramic Obtained by Peroxomethod

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ABSTRACT. The system $(1-x)\text{Ba}_{0.7}\text{Sr}_{0.3}\text{TiO}_3 \cdot x\text{MgZrO}_3$ where $x=0.15; 0.20; 0.25; 0.30; 0.35$ mol at calcination temperature $T=1300; 1350; 1400^\circ\text{C}$ for 4 hours was synthesized. The most important electric characteristics: relative dielectric permittivity (ϵ_r), dielectric losses ($\tan \delta$) and specific volume resistivity (ρ_v) were studied at frequency 1 kHz. The system $0.7\text{Ba}_{0.7}\text{Sr}_{0.3}\text{TiO}_3 \cdot 0.35\text{MgZrO}_3$ has $\epsilon_r=1050$, low dielectric losses $\tan \delta=42 \cdot 10^{-4}$, in the temperature range $20-120^\circ\text{C}$ temperature coefficient of the permittivity $\text{TK}_{\epsilon_r} \rightarrow 0$, and $\rho_v=10^8 \Omega \text{ cm}$. Those values make it suitable for production of thermal stability capacitors as well as capacitors with low dielectric losses working at high frequencies.

ИЗСЛЕДВАНЕ ДИЕЛЕКТРИЧНИТЕ СВОЙСТВА НА $(1-x)\text{Ba}_{0.7}\text{Sr}_{0.3}\text{TiO}_3 \cdot x\text{MgZrO}_3$. КЕРАМИКА ПОЛУЧЕНА ПО ПЕРОКСОМЕТОД

РЕЗЮМЕ. Получена е по пероксо метод системата $(1-x)\text{Ba}_{0.7}\text{Sr}_{0.3}\text{TiO}_3 \cdot x\text{MgZrO}_3$. Изследвани са най-важните електрични характеристики: диелектричната проникваемост (ϵ_r) и диелектричните загуби ($\tan \delta$), обемно специфично съпротивление (ρ_v) при честота 1kHz за следния температурен режим на изпичане на керамиката: $1300, 1350, 1400^\circ\text{C}$ за време 4 часа. Керамичния материал със състав $0.7\text{Ba}_{0.7}\text{Sr}_{0.3}\text{TiO}_3 \cdot 0.3\text{MgZrO}_3$ изпечен при 1400°C има $\epsilon_r=1050$, ниски диелектрични загуби $\tan \delta=42 \cdot 10^{-4}$, за температурния интервал от 20 до 120°C има температурен коефициент на диелектричната проникваемост $\text{TK}_{\epsilon_r} \rightarrow 0$ и $\rho_v=10^8 \Omega \text{ cm}$. Тези данни го правят подходящ за производството на термостабилни кондензатори, както и за кондензатори с ниски диелектрични загуби.

Introduction

The investigation aims to study the materials suitable for the production of thermal stability capacitors with low dielectric losses. In many publications by substitution of BaTiO_3 with: CaTiO_3 , SrTiO_3 (Tabata and Kawai, 1997; Cramer et al., 2003), MgTiO_3 (Parvanova, 2002), Nd_2O_3 (Kohler et al., 1996), Bi_2O_3 (Yi Zhi et al., 1998), ZnTiO_3 , NiTiO_3 (Parvanova, 2002), La_2O_3 , Cr_2O_3 (Fukunaga et al., 2003; Wang et al., 2001) it is achieved to smoothen the maximum of the dielectric permittivity (ϵ_r) in the range of the Curie temperature and decrease the dielectric losses.

The system $\text{Ba}_{0.7}\text{Sr}_{0.3}\text{TiO}_3$ is obtained by the peroxomethod. By adding different concentration of MgZrO_3 the last mentioned properties is aimed to be attained. In the reference data about the synthesis and the dielectric properties of the system $(1-x)\text{Ba}_{0.7}\text{Sr}_{0.3}\text{TiO}_3 \cdot x\text{MgZrO}_3$ is missing. The synthesized material is of scientific and practical interest to be studied as it has been obtained by peroxomethod. This method has a lot of advantages in comparison with the classical ones. The temperature of synthesis is considerably lower, the obtained titanates has higher purity, they are fine crystalline with homogeneous grain-size composition.

Experimental

The starting BaTiO_3 and SrTiO_3 were prepared by peroxomethod (Genov et al., 1988; Maneva and Parvanova, 1995). The peroxomethod is based the interaction of TiCl_4 solution and 17% solution of BaCl_2 and $\text{Sr}(\text{NO}_3)_2$ and H_2O_2 and NH_3 solution up to $\text{pH}=9$. The obtained intermediate

peroxocompounds in the process of the reaction are amorphous precipitate. They were calcinated respectively at $T=600^\circ\text{C}$ for BaTiO_3 and $T=650^\circ\text{C}$ for SrTiO_3 . The size of the particles is less than $1\mu\text{m}$ and no milling is needed. The titanates were proved by x-ray investigation with TUR-U-62 apparatus. MgZrO_3 is obtained by classical methods. MgO and ZrO_2 with 99% purity were used. The last mentioned were calcinated at 1400°C for 4 hours. The obtained MgZrO_3 was milled in planetary ball mill. A system with the composition $(1-x)\text{Ba}_{0.7}\text{Sr}_{0.3}\text{TiO}_3 \cdot x\text{MgZrO}_3$ where $x=0.15; 0.20; 0.25; 0.30; 0.35$ mol was obtained.

The powders were pressed at $P=200 \cdot 10^5 \text{ Pa}$. 10% polyvinyl alcohol is used as a plastificator. 6 mm high discs with 10mm diameter were prepared. They were calcinated at $T_{\text{cal}}=1300; 1350$ and 1400°C for 4 hours on air. The temperature $T_{\text{cal}}=360^\circ\text{C}$ was kept for half an hour to evaporate the plastificator. Aiming to provide a good contact during the electric measurements the discs were metaled with silver paste. The temperature dependence of the capacity and dielectric losses ($\tan \delta$) were tested at a frequency of 1 kHz by using a General Radio impedance meter (model 1687). The temperature dependence of the capacity was measured in a Heraeus Votsch temperature chamber in a temperature range from 20°C to $+120^\circ\text{C}$ at steps of 5°C .

Result and discussion

The dependence between the relative dielectric permittivity at $T=20^\circ\text{C}$ for the system composition and the calcination temperature is presented on fig.1 from the figure it is obvious that ϵ_r at $T=20^\circ\text{C}$ strongly depends on the ceramic composition

and at $x=0.15$ mol it has maximum value. However, over the given the value for "x" the dielectric permittivity decreases monotonously and it is explained by the increasing of MgZrO_3 concentration having considerably lower ϵ_r . The composition $0.65\text{Ba}_{0.7}\text{Sr}_{0.3}\text{TiO}_3 \cdot 0.35\text{MgZrO}_3$ has times lower $\epsilon_r=1050$ in comparison with $\text{Ba}_{0.7}\text{Sr}_{0.3}\text{TiO}_3$ ($\epsilon_r=3450$ according the data by Parvanova 2002). On the figure it is seen that the dielectric permittivity slightly depends on the temperature of calcination. It has maximum value at 1400°C $\epsilon_r=3400$. $T_{\text{cal}}=1300^\circ\text{C}$ is insufficient for the formation of isomorphous structure of the ceramic ($\epsilon_r=2100$).

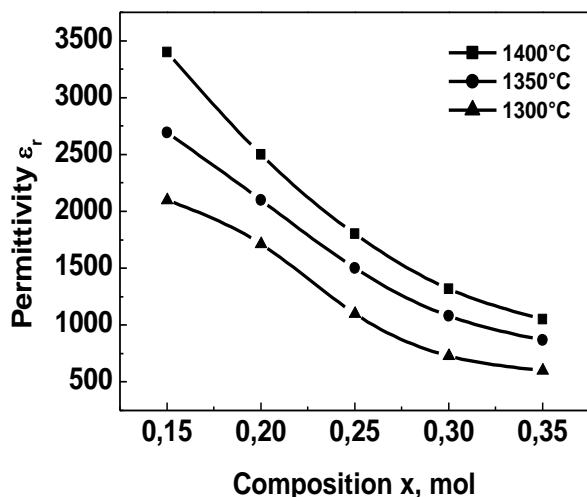


Fig. 1. Dependence of the dielectric permittivity ϵ_r of the materials on the concentration of MgZrO_3 and calcination temperature

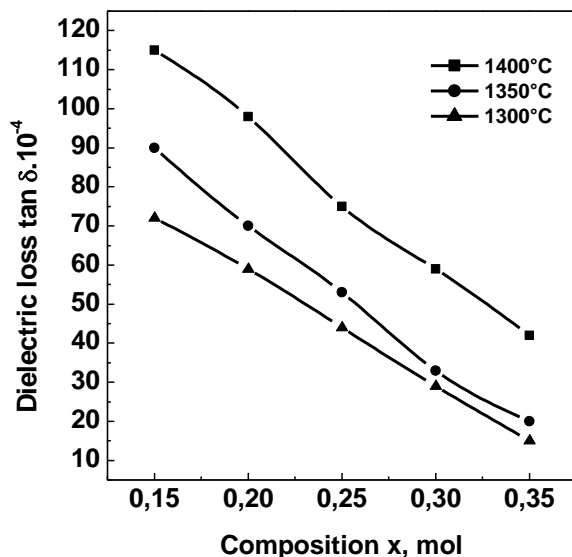


Fig. 2. Dependence of the dielectric losses $\tan \delta$ of the materials on the concentration of MgZrO_3 and calcination temperature

The graphical dependence between the dielectric losses of the system composition and calcination temperature is given on fig.2. It is seen on it that the losses follow the pattern of the dielectric permittivity. It is known that MgZrO_3 has low dielectric losses. That is why the system $(1-x)\text{Ba}_{0.7}\text{Sr}_{0.3}\text{TiO}_3 \cdot x \text{MgZrO}_3$ would have decreasingly losses having increased the MgZrO_3 concentration. The increased dielectric losses having

increased the temperature of calcination probably due to the structure defects caused by the high temperature calcination ($T_{\text{cal}}=1400^\circ\text{C}$). Similar dependence is discussed by Jlin and Wu, 1990. The increasing of the ceramic conductivity is also confirmed by fig.3. It shows the dependence between the specific volume resistivity at the temperature of calcination and the system composition (x). It is seen on the figure that ρ_v depends at the same extent on T_{cal} and on the composition of the studied system. Having compared fig. 2 and 3 it is seen that the dielectric losses are mostly losses of conductivity. The temperature dependence between the relative dielectric permittivity and the system composition at $T_{\text{cal}}=1400^\circ\text{C}$ is presented on fig. 4. It follows from the figure that increasing the "x" value the maximum of the Curie temperature gradually decreases and it seems that the depressor character of MgZrO_3 is observed. It leads to improving the temperature stability of the capacitors.

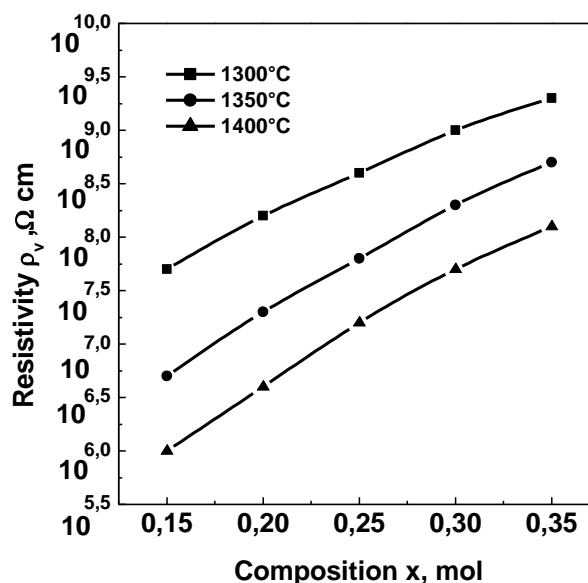


Fig. 3. Dependence of the resistivity ρ_v of materials on the concentration of MgZrO_3 and calcination temperature

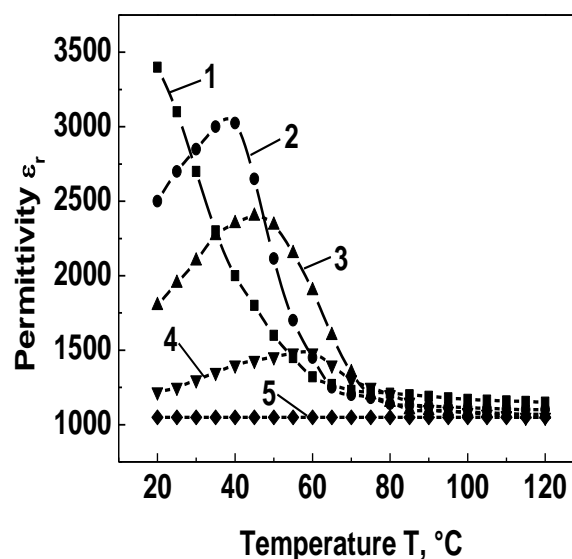


Fig. 4. Dependence of the dielectric permittivity ϵ_r on the concentration of the MgZrO_3 calcinated at a temperature of 1400°C ; 1) $x=0.15$ mol; 2) $x=0.20$ mol; 3) $x=0.25$ mol; 4) $x=0.30$ mol; 5) $x=0.35$ mol

The substitution of BaTiO₃ with SrTiO₃ lead to the Curie temperature to the lower values. Similar dependence is discussed by Parvanova 2003. For x=0.35 mol the relative dielectric permittivity is constant with the temperature change i.e. temperature coefficient of dielectric permittivity $TK_{\epsilon_r} \rightarrow 0$. The composition x=0.30 mol in the range of 20-80°C has $TK_{\epsilon_r}=5200.10^{-6} \text{ } ^\circ\text{C}^{-1}$.

The system 0.65Ba_{0.7}Sr_{0.3}TiO₃.0.35MgZrO₃ obtained at T_{cal}=1400°C is suitable for the production of thermal stability capacitors with low dielectric losses. The system in the temperature range 20-120°C has $\epsilon_r=1050$, $TK_{\epsilon_r} \rightarrow 0$ and very good dielectric losses $\tan\delta=42.10^{-4}$.

Conclusion

The system (1-x)Ba_{0.7}Sr_{0.3}TiO₃.x MgZrO₃ where x=0.15; 0.20; 0.25; 0.30; 0.35 mol at calcination temperature T=1300; 1350; 1400°C for 4 hours was synthesized.

The most important electric characteristics relative dielectric permittivity (ϵ_r), dielectric losses ($\tan \delta$) and specific volume resistivity (ρ_v) were studied.

The system 0.7Ba_{0.7}Sr_{0.3}TiO₃.0.35MgZrO₃ has $\epsilon_r=1050$, low dielectric losses $\tan\delta=42.10^{-4}$, in the temperature range 20-120°C $TK_{\epsilon_r} \rightarrow 0$, and $\rho_v=10^8 \text{ } \Omega \text{ cm}$. Those values make it suitable for production of thermal stability capacitors as well as capacitors with low dielectric losses working at high frequencies.

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